

Abdullah Giray Yağlıkçı

Researcher at SAFARI Research Group in ETH Zurich



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Up-to-date version of CV is available at <https://agyaglikci.github.io/agyaglikci.github>

I am a researcher at the [Safari Research Group](#) in [ETH Zürich](#), working with [Prof. Onur Mutlu](#). My current broader research interests are in computer architecture, systems, and hardware security with a special focus on DRAM robustness and performance. In particular, my PhD research focuses on understanding and solving the RowHammer vulnerability. I have published several works on this topic in major venues such as HPCA, MICRO, ISCA, DSN, and SIGMETRICS. Among these works, BlockHammer was named as a finalist by Intel in 2022 for the Intel Hardware Security Academic Award [🏆](#), Svärd received first place in the ACM SRC at PACT 2023 [🏆](#), and my dissertation was recently selected as one of the five finalists in the HOST 2024 PhD dissertation competition [🏆](#). My RowHammer research is in part supported by Google Security and Privacy Research Award and the Microsoft Swiss Joint Research Center.

Education

2024

PhD

ETH Zürich

2016

MSc

University of Notre Dame Du Lac (ND)

2014

MSc

TOBB University of Economics and Technology

2011

BSc

TOBB University of Economics and Technology

First-Author Publications

Enabling Efficient and Scalable DRAM Read Disturbance Mitigation via New Experimental Insights into Modern DRAM Chips in PhD Thesis, ETH Zürich, 2024

Full Reference: A. Giray Yağlıkçı, "Enabling Efficient and Scalable DRAM Read Disturbance Mitigation via New Experimental Insights into Modern DRAM Chips," ETH Zürich, 2024.

This PhD dissertation, based on my PhD research, demonstrates that we can mitigate DRAM read disturbance efficiently and scalably by 1) building a detailed understanding of DRAM read disturbance, 2) leveraging insights into modern DRAM chips and memory controllers, and 3) devising novel solutions that do not require proprietary knowledge of DRAM chip internals. This thesis comprehensively explains the cutting edge in DRAM read disturbance research as of August, 2024, and identifies future research avenues to address the outstanding and emerging challenges in the field.

Dissertation: [📄](#)

Defense Slides: [📄](#)

rowhammer

defense

refresh

memory

dram

memory controller

subarray

parallelism

spatial

variation

temperature

access pattern


rowpress



Spatial Variation-Aware Read Disturbance Defenses in HPCA 2024

Full Reference: A. Giray Yağlıkçı, Yahya Can Tuğrul, Geraldo F. Oliveira, İsmail Emir Yüksel, Ataberk Olgun, Haocong Luo, Onur Mutlu "Spatial Variation-Aware Read Disturbance Defenses: Experimental Analysis of Real DRAM Chips and

Implications on Future Solutions" Proceedings of the 30th IEEE International Symposium on High-Performance Computer Architecture (HPCA-30), 2024.

We tackle the performance overhead of existing read disturbance solutions by leveraging the spatial variation in read disturbance across different memory locations in real DRAM chips. To do so, we 1) present the first rigorous real DRAM chip characterization study of spatial variation of read disturbance and 2) propose Svård, a new mechanism that dynamically adapts the aggressiveness of existing solutions based on the row-level read disturbance profile. Our experimental characterization on 144 real DDR4 DRAM chips representing 10 chip designs demonstrates a large variation in read disturbance vulnerability across different memory locations: in the part of memory with the worst read disturbance vulnerability, 1) up to 2x the number of bitflips can occur and 2) bitflips can occur at an order of magnitude fewer accesses, compared to the memory locations with the least vulnerability to read disturbance. Svård leverages this variation to reduce the overheads of five state-of-the-art read disturbance solutions, and thus significantly increases system performance.

Full Paper: 

Live Talk:  

rowhammer

defense

refresh

memory

dram

memory controller

subarray

parallelism


spatial



variation



HiRA: Hidden Row Activation for Reducing Refresh Latency of Off-the-Shelf DRAM Chips in MICRO 2022

Full Reference: [A. Giray Yağlıkcı](#), Ataberk Olgun, Minesh Patel, Haocong Luo, Hasan Hassan, Lois Orosa, Oguz Ergin, and Onur Mutlu, "HiRA: Hidden Row Activation for Reducing Refresh Latency of Off-the-Shelf DRAM Chips" Proceedings of the 55th International Symposium on Microarchitecture (MICRO), Chicago, IL, USA, October 2022.

We propose a new operation, Hidden Row Activation (HiRA), and the HiRA Memory Controller (HiRA-MC) to perform HiRA operations. HiRA hides a refresh operation's latency by refreshing a row concurrently with accessing or refreshing another row within the same bank. Unlike prior works, HiRA achieves this parallelism without any modifications to off-the-shelf DRAM chips. To do so, it leverages the new observation that two rows in the same bank can be activated without data loss if the rows are connected to different charge restoration circuitry. HiRA reduces the time spent on refresh operations by 51.4%. HiRA-MC increases system performance by 12.6% and 3.73x as it reduces the performance degradation due to periodic refreshes and refreshes for RowHammer protection (preventive refreshes), respectively, for future DRAM chips with increased density and RowHammer vulnerability.

Full Paper: 

Live Talk Slides:  

Lecture (36 mins):  

rowhammer

defense

refresh

memory

dram

memory controller


subarray

parallelism

Understanding RowHammer Under Reduced Wordline Voltage in DSN 2022



Full Reference: [A. Giray Yağlıkcı](#), Haocong Luo, Geraldo F. de Oliveira, Ataberk Olgun, Minesh Patel, Jisung Park, Hasan Hassan, Jeremie S. Kim, Lois Orosa, and Onur Mutlu, "Understanding RowHammer Under Reduced Wordline Voltage: An Experimental Study Using Real DRAM Devices" Proceedings of the 52nd Annual IEEE/IFIP International Conference on Dependable Systems and Networks (DSN), Baltimore, MD, USA, June 2022.

This is the first work to experimentally demonstrate on 272 real DRAM chips that lowering VPP reduces a DRAM chip's RowHammer vulnerability. We show that lowering VPP 1) increases the number of activate-precharge cycles needed to induce a RowHammer bit flip by up to 85.8 % with an average of 7.4 % across all tested chips and 2) decreases the RowHammer bit error rate by up to 66.9 % with an average of 15.2 % across all tested chips. At the same time, reducing VPP marginally worsens a DRAM cell's access latency, charge restoration, and data retention time within the guardbands of system-level nominal timing parameters for 208 out of 272 tested chips. We conclude that reducing VPP is a promising strategy for reducing a DRAM chip's RowHammer vulnerability without requiring modifications to DRAM chips.

Full Paper: 

arXiv: 

Lightning Talk (2 mins):  

Full Talk (34 mins incl. Q&A):  

rowhammer

characterization

real chips

memory

dram

voltage


wordline

A Deeper Look into RowHammer in MICRO 2021

Full Reference: Lois Orosa, [Abdullah Giray Yağlıkcı](#), Haocong Luo, Ataberk Olgun, Jisung Park, Hasan Hassan, Minesh Patel, Jeremie S. Kim, and Onur Mutlu, "A Deeper Look into RowHammer's Sensitivities: Experimental Analysis of Real

DRAM Chips and Implications on Future Attacks and Defenses" Proceedings of the 54th International Symposium on Microarchitecture (MICRO), Virtual, October 2021.








We present an experimental characterization using 248 DDR4 and 24 DDR3 modern DRAM chips from four major DRAM manufacturers demonstrating how the RowHammer effects vary with three fundamental properties: 1) DRAM chip temperature, 2) aggressor row active time, and 3) victim DRAM cell's physical location. Among our 16 new observations, we highlight that a RowHammer bit flip 1) is very likely to occur in a bounded range, specific to each DRAM cell (e.g., 5.4% of the vulnerable DRAM cells exhibit errors in the range 70 °C to 90 °C), 2) is more likely to occur if the aggressor row is active for longer time (e.g., RowHammer vulnerability increases by 36% if we keep a DRAM row active for 15 column accesses), and 3) is more likely to occur in certain physical regions of the DRAM module under attack (e.g., 5% of the rows are 2x more vulnerable than the remaining 95% of the rows). Our study has important practical implications on future RowHammer attacks and defenses. We describe and analyze the implications of our new findings by proposing three future RowHammer attack and six future RowHammer defense improvements.

Full Paper:  arXiv:  Lightning Talk (1.5 mins):   Full Talk (21 mins):  
rowhammer characterization real chips memory dram temperature access pattern spatial variation

BlockHammer: Preventing RowHammer at Low Cost by Blacklisting Rapidly-Accessed DRAM Rows in HPCA 2021

Full Reference: A. Giray Yağlıkçı, Minesh Patel, Jeremie S. Kim, Roknoddin Azizi, Ataberk Olgun, Lois Orosa, Hasan Hassan, Jisung Park, Konstantinos Kanellopoulos, Taha Shahroodi, Saugata Ghose, and Onur Mutlu, **"BlockHammer: Preventing RowHammer at Low Cost by Blacklisting Rapidly-Accessed DRAM Rows,"** in Proceedings of the 27th International Symposium on High-Performance Computer Architecture (HPCA), Virtual, February-March 2021.

In this paper, we show that it is possible to efficiently and scalably prevent RowHammer bitflips without knowledge of or modification to DRAM internals. We introduce BlockHammer, a low-cost, effective, and easy-to-adopt RowHammer mitigation mechanism that prevents all RowHammer bitflips while overcoming the two key challenges: scalability with worsening RowHammer vulnerability and compatibility with commodity DRAM chips. BlockHammer selectively throttles memory accesses that may cause RowHammer bitflips. To our knowledge, this is the first work that prevents RowHammer bitflips efficiently and scalably without knowledge of or modifications to DRAM internals.

Full Paper:  Short Talk (7 mins):   Full Talk (22 mins):   Intel HWSec Academic Awards Talk (2 mins):  
rowhammer defense throttling memory dram memory controller hardware

Research Talks

Lecture in EFCL Summer School

Memory Latency, Data Retention, and Refresh

🕒 90 mins | Video:  | Slides:  

Lecture in ETH Zurich

DRAM Robustness and RowHammer Lecture (Second half of the lecture)

🕒 1 hour | Video:  | Slides:  

HOST 2024

Blinded PhD Research Summary

🕒 23 mins | Video:  | Slides:  

SAFARI Live Seminar

A Deeper Look into RowHammer's Characteristics in Real Modern DRAM Chips

🕒 1 hour 50 mins | Video:  | Slides:  



SAFARI Live Seminar

Efficiently and Scalably Mitigating RowHammer in DRAM-Based Memory Systems

🕒 2 hours 4 mins | Video:  | Slides:  

MICRO 2023

PhD Research Summary

🕒 3 mins | Video:  | Slides:  

Lecture in ETH Zurich

Memory Security, Reliability, Safety Problems and Solutions

🕒 2 hours 50 mins | Video:  | Slides:  

ASP-DAC 2023

Fundamentally Understanding and Solving RowHammer

🕒 26 mins | Video:  | Slides:  




AMLD 2022

Fundamentally Understanding and Solving RowHammer

🕒 20 mins | Video:  | Slides:  

P&S DRAM Bender, ETH Zurich

A Deeper Look into RowHammer's Sensitivities

🕒 1 hour | Video:  | Slides:  

Employment

Apr 2024 - Present

Researcher - ETH Zürich

Feb 2018 - Apr 2024

Research and Teaching Assistant - ETH Zürich

Aug 2017 - Feb 2018

Research Intern - Intel Labs Santa Clara

Aug 2016 - Aug 2017

Research Intern - Carnegie Mellon University (CMU)

Aug 2014 - Aug 2016

Research Assistant - University of Notre Dame Du Lac (ND)

Jan 2012 - Aug 2014

Research and Teaching Assistant - TOBB University of Economics and Technology (TOBB ETÜ)

May 2011 - Dec 2011

Electrical Design Engineer - Kasirga Information Systems

May 2010 - Apr 2011

Electrical Design Engineer - Yumruk Space and Defense Industry

Service

2023

Student Assistant to PC chairs for DSN
Reviewer for DSN

2022
Reviewer for TODAES
Subreviewer for ASPLOS, DSN, ISCA, CAL, DRAMSec, TC, TCAD, and USENIX ATC

2021
Subreviewer for HPCA, MICRO, TCAD, and USENIX ATC



2020
Subreviewer for DSN, ISCA, MICRO, CCS, ISCAS, ISPASS, NVMW, and TCSI

2019
Subreviewer for DSN, ISCA, MICRO, MSST, TCAD, and TED


2018
Subreviewer for ASPLOS, HPCA, PACT, Nature Electronics, TC, and TVLSI

2017
Subreviewer for DSN, MICRO, ISCA, and PLDI




Other Publications



Geraldo F. Oliveira, Ataberk Olgun, Abdullah Giray Yaglikçi, F. Nisa Bostanci, Juan Gómez-Luna, Saugata Ghose, Onur Mutlu, **"MIMDRAM: An End-to-End Processing-Using-DRAM System for High-Throughput, Energy-Efficient and Programmer-Transparent Multiple-Instruction Multiple-Data Computing"** Proceedings of the 28th International Symposium on High-Performance Computer Architecture (HPCA), Edinburgh, UK, March 2024. [Full Paper:](#)  [Extended Version:](#) 

[Source Code:](#) 




Haocong Luo, Ataberk Olgun, [A. Giray Yaglikci](#), Yahya Can Tugrul, Steve Rhyner, M. Banu Cavlak, Joel Lindegger, Mohammad Sadrosadati, and Onur Mutlu, **"RowPress: Amplifying Read Disturbance in Modern DRAM Chips"** Proceedings of the 50th International Symposium on Computer Architecture (ISCA), Orlando, FL, USA, June 2023. [Full Paper:](#) 


[Extended Version:](#)  [Lightning Talk \(3 mins\):](#)   [Full Talk \(26 mins\):](#)   [Source Code:](#) 


Ataberk Olgun, Majd Osserian, [A. Giray Yaglikci](#), Yahya Can Tugrul, Haocong Luo, Steve Rhyner, Behzad Salami, Juan Gomez-Luna, and Onur Mutlu, **"An Experimental Analysis of RowHammer in HBM2 DRAM Chips"** Proceedings of the 53rd Annual IEEE/IFIP International Conference on Dependable Systems and Networks Disrupt Track (DSN Disrupt), Porto, Portugal, June 2023. [Full Paper:](#)  [Full Talk \(26 mins\):](#)  

Ataberk Olgun, Hasan Hassan, [A. Giray Yaglikci](#), Yahya Can Tuğrul, Lois Orosa, Haocong Luo, Minesh Patel, Oguz Ergin, Onur Mutlu, **"DRAM Bender: An Extensible and Versatile FPGA-based Infrastructure to Easily Test State-of-the-art DRAM Chips"** IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2023. [Full Paper:](#)  [Source Code:](#) 

Onur Mutlu, Ataberk Olgun, and [A. Giray Yağlıkçi](#), **"Fundamentally Understanding and Solving RowHammer"** Invited Special Session Paper at the 28th Asia and South Pacific Design Automation Conference (ASP-DAC), Tokyo, Japan, January 2023.

[Full Paper:](#)  [Recorded Talk \(26 mins\):](#)  

F. Nisa Bostanci, Ataberk Olgun, Lois Orosa, [A. Giray Yağlıkçi](#), Jeremie S. Kim, Hasan Hassan, Oguz Ergin, and Onur Mutlu, **"DR-STRaNGe: End-to-End System Design for DRAM-based True Random Number Generators"** Proceedings of the 28th International Symposium on High-Performance Computer Architecture (HPCA), Virtual, April 2022. [Full Paper:](#) 

[Full Talk \(24 mins\):](#)  

Jawad Haj Yahya, Jeremie S. Kim, [A. Giray Yağlıkçi](#), Jisung Park, Efraim Rotem, Yanos Sazeides, and Onur Mutlu, **"DarkGates: A Hybrid Power-Gating Architecture to Mitigate the Performance Impact of Dark-Silicon in High Performance**

Processors" Proceedings of the 28th International Symposium on High-Performance Computer Architecture (HPCA), Virtual, April 2022. [Full Paper: pdf](#) [Slides: pdf](#)

Ataberk Olgun, Minesh Patel, [A. Giray Yağlıkçı](#), Haocong Luo, Jeremie S. Kim, F. Nisa Bostanci, Nandita Vijaykumar, Oguz Ergin, and Onur Mutlu, **"QUAC-TRNG: High-Throughput True Random Number Generation Using Quadruple Row Activation in Commodity DRAM Chips"** Proceedings of the 48th International Symposium on Computer Architecture (ISCA), Virtual, June 2021. [Full Paper: pdf](#) [Full Talk \(25 mins\): pdf](#) [SAFARI Live Seminar \(1 hr 26 mins\): pdf](#)

Jawad Haj-Yahya, Jeremie S. Kim, [A. Giray Yağlıkçı](#), Ivan Puddu, Lois Orosa, Juan Gomez Luna, Mohammed Alser, and Onur Mutlu, **"IChannels: Exploiting Current Management Mechanisms to Create Covert Channels in Modern Processors"** Proceedings of the 48th International Symposium on Computer Architecture (ISCA), Virtual, June 2021. [Full Paper: pdf](#)
[Full Talk \(21 mins\): pdf](#)

Jeremie S. Kim, Minesh Patel, [A. Giray Yağlıkçı](#), Hasan Hassan, Roknoddin Azizi, Lois Orosa, and Onur Mutlu, **"Revisiting RowHammer: An Experimental Analysis of Modern Devices and Mitigation Techniques,"** in Proceedings of the 47th International Symposium on Computer Architecture (ISCA), Valencia, Spain, June 2020. [Full Paper: pdf](#)
[Full Talk \(20 mins\): pdf](#) [Lecture \(55 mins\): pdf](#)

Haocong Luo, Taha Shahroodi, Hasan Hassan, Minesh Patel, [A. Giray Yağlıkçı](#), Lois Orosa, Jisung Park, and Onur Mutlu, **"CLR-DRAM: A Low-Cost DRAM Architecture Enabling Dynamic Capacity-Latency Trade-Off,"** in Proceedings of the 47th International Symposium on Computer Architecture (ISCA), Valencia, Spain, June 2020. [Full Paper: pdf](#)
[Full Talk \(20 mins\): pdf](#)

Jawad Haj-Yahya, Mohammed Alser, Jeremie Kim, [A. Giray Yağlıkçı](#), Nandita Vijaykumar, Efraim Rotem, and Onur Mutlu, **"SysScale: Exploiting Multi-domain Dynamic Voltage and Frequency Scaling for Energy Efficient Mobile Processors,"** in Proceedings of the 47th International Symposium on Computer Architecture (ISCA), Valencia, Spain, June 2020. [Full Paper: pdf](#) [Full Talk \(17 mins\): pdf](#)

Skanda Koppula, Lois Orosa, [A. Giray Yağlıkçı](#), Roknoddin Azizi, Taha Shahroodi, Konstantinos Kanellopoulos, and Onur Mutlu, **"EDEN: Energy-Efficient, High-Performance Neural Network Inference Using Approximate DRAM,"** in Proceedings of the 52nd International Symposium on Microarchitecture (MICRO), Columbus, OH, USA, October 2019. [Full Paper: pdf](#)
[Lecture \(38 mins\): pdf](#) [Lightning Talk: pdf](#)

H. Hassan, M. Patel, J. S. Kim, [A. Giray Yağlıkçı](#), N. Vijaykumar, N. Mansouri Ghiasi, S. Ghose, O. Mutlu, **"CROW: A Low-Cost Substrate for Improving DRAM Performance, Energy Efficiency, and Reliability,"** in Proceedings of the International Symposium on Computer Architecture (ISCA), June 2019. [Full Paper: pdf](#) [Full Talk: pdf](#) [Lightning Talk: pdf](#)

S. Ghose, [A. Giray Yağlıkçı](#), R. Gupta, D. Lee, K. Kudrolli, W. X. Liu, H. Hassan, K. K. Chang, N. Chatterjee, A. Agrawal, M. O'Connor, and O. Mutlu, **"What Your DRAM Power Models Are Not Telling You: Lessons from a Detailed Experimental Study,"** in Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (SIGMETRICS), Irvine, CA, USA, June 2018. [Abstract: pdf](#) [Full Paper: pdf](#) [POMACS Journal Version: pdf](#) [Slides: pdf](#)

K. Chang, [A. Giray Yağlıkçı](#), S. Ghose, A. Agrawal, N. Chatterjee, A. Kashyap, D. Lee, M. O'Connor, H. Hassan, and O. Mutlu, **"Understanding Reduced-Voltage Operation in Modern DRAM Devices: Experimental Characterization, Analysis, and Mechanisms,"** in Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (SIGMETRICS), Urbana-Champaign, IL, USA, June 2017. [Abstract: pdf](#) [Full Paper: pdf](#) [POMACS Journal Version: pdf](#)
[Slides: pdf](#)

[A. Giray Yağlıkçı](#), Jeremie S. Kim, Fabrice Devaux, and Onur Mutlu, **"Security Analysis of the Silver Bullet Technique for RowHammer Prevention,"** arXiv, 2021. [Full Paper: pdf](#)

Hall of Fame Stats:

[HPCA: 6 papers](#)

[MICRO: 3 papers](#)

[ISCA: 7 papers](#)

[DSN: 4 papers](#)

[SIGMETRICS: 2 papers](#)

